



ZXTP56060FDBQ

60V DUAL PNP LOW V_{CE(sat)} TRANSISTOR

Description

This bipolar junction transistors (BJT) is designed to meet the stringent requirements of automotive applications.

Features

- BV_{CEO} > -60V
- I_C = -2A High Continuous Collector Current
- $R_{CE(sat)} = 250 m\Omega$ for a Low Equivalent On-Resistance
- Sidewall Tin Plating for Wettable Flanks in AOI
- P_D Up to 2.47W for Power Demanding Applications
- Low Profile 0.6mm High Package for Thin Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The ZXTP56060FDBQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/guality/product-definitions/

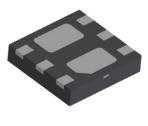
Mechanical Data

- Case: U-DFN2020-6 (SWP) (Type A) with Sidewall Plating
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin, Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.0065 grams (Approximate)

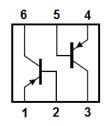
Application

- Matrix LED Lighting
- Power Management

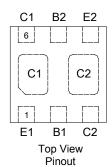
U-DFN2020-6 (S	SWP) (Type A)
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Bottom View



Device Symbol



Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
ZXTP56060FDBQ-7	2D9	7	8	3000
ZXTP56060FDBQ-13R	2D9	13	8	10,000

1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

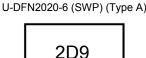
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

Notes:



YWX

2D9 = Product Type Marking Code Y = Year: 0~9 W = Week: A~Z: 1~26 week; a~z: 27~52 week; z represents 52 and 53 week X = A~Z: Internal code



Absolute Maximum Ratings – Q1 & Q2 (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-2	A
Peak Pulse Collector Current	I _{CM}	-3	A
Base Current	IB	-300	mA
Peak Base Current	I _{BM}	-1	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
	(Notes 5 & 7)		405		
Devuer Dissinction	(Notes 5 & 8)	P	510	mW	
Power Dissipation	(Notes 6 & 7)	PD	1650		
	(Notes 6 & 8)		2470		
	(Notes 5 & 7)		308		
Thermal Resistance, Junction to Ambient	(Notes 5 & 8)	P	245	°C/W	
	(Notes 6 & 7)	$R_{ ext{ heta}JA}$	76	C/W	
	(Notes 6 & 8)		51		
Thermal Resistance, Junction to Lead	(Note 9)	$R_{ ext{ heta}JL}$	18	°C/W	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C	

ESD Ratings (Note 10)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

Notes: 5. For a device mounted with the exposed collector pads on minimum recommended pad layout that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.

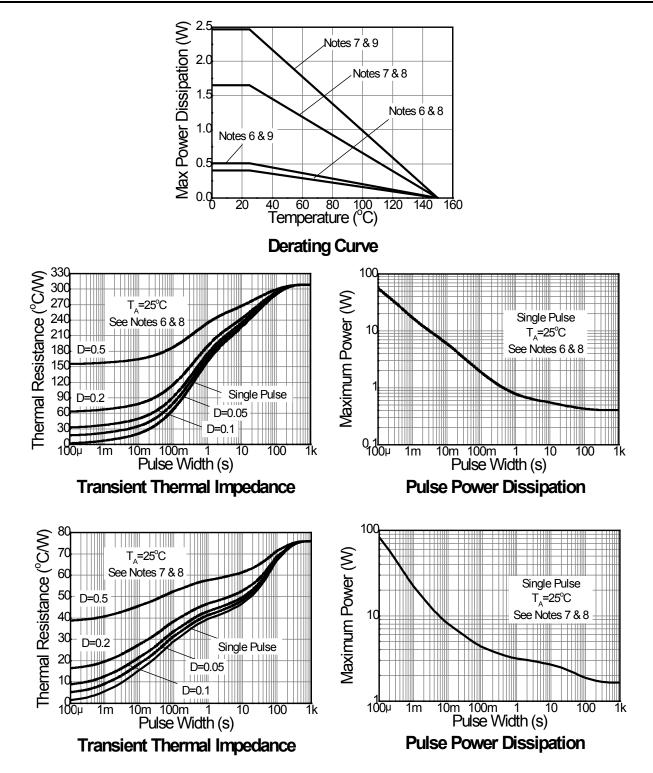
6. Same as Note 5, except the device is mounted with the collector pad on 28mm × 28mm (8cm²) 2oz copper.

7. For a dual device with one active die.

For dual device with two active die running at equal power.
Thermal resistance from junction to solder-point (on the exposed collector pads).
Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





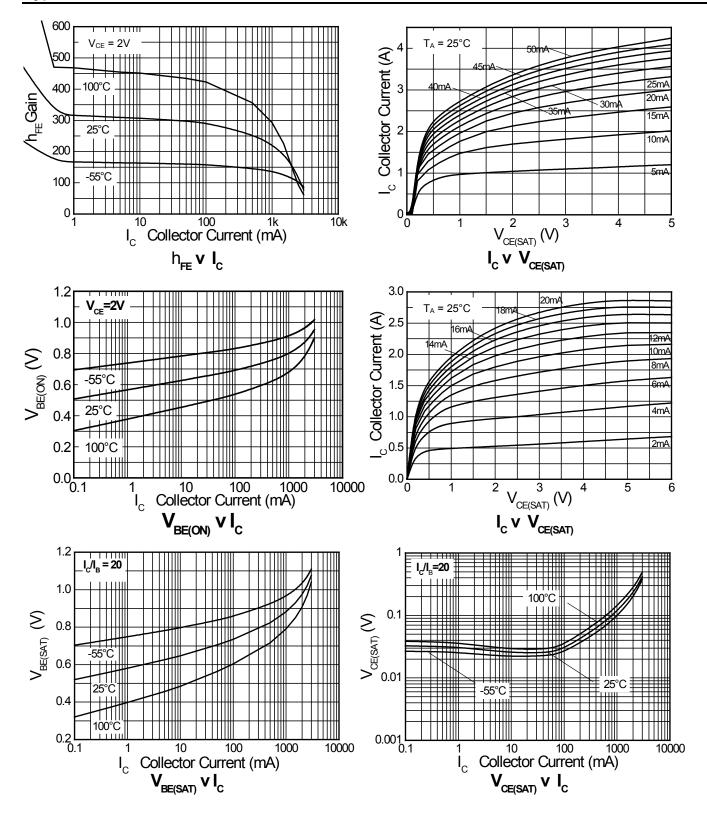
Electrical Characteristics – Q1 & Q2 (@T_A = +25°C, unless otherwise specified.)

Characteristic	Currada a l	Min	Turn	Max	L lucit	Test Conditions
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV _{CBO}	-60	—	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 11)	BV _{CEO}	-60		—	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BVEBO	-7	—	-	V	I _E = -100μA
Collector-Base Cutoff Current	lana		_	-100	nA	$V_{CB} = -48V, I_E = 0$
	I _{CBO}	_	—	-50	μA	V _{CB} = -48V, I _E = 0, T _A = +150°C
Emitter-Base Cutoff Current	I _{EBO}	_	—	-100	nA	V _{EB} = -5.6V, I _C = 0
		170	—	—		V _{CE} = -2V, I _C = -100mA
DC Current Gain (Note 11)	h _{FE}	140	—	—		V_{CE} = -2V, I_{C} = -500mA
	TIFE	110	—	—		$V_{CE} = -2V, I_{C} = -1A$
		50	—	—		$V_{CE} = -2V, I_{C} = -2A$
		_	—	-120		I _C = -500mA, I _B = -50mA
Callester Erritter Caturation Mathema (Nate 11)	V _{CE(sat)}	_	—	-250	mV	I _C = -1A, I _B = -50mA
Collector-Emitter Saturation Voltage (Note 11)		_	—	-420		I _C = -0.7A, I _B = -7mA
			—	-450		I _C = -2A, I _B = -200mA
Equivalent On-Resistance (Note 11)	R _{CE(sat)}	_	—	250	mΩ	I _E = -1A, I _B = -50mA
			—	-1	V	I _C = -0.5A, I _B = -50mA
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}		—	-1		I _C = -1A, I _B = -50mA
			—	-1.25		I _C = -2A, I _B = -200mA
Base-Emitter Turn-on Voltage (Note 11)	V _{BE(on)}		—	-0.9	V	$V_{CE} = -2V, I_{C} = -0.5A$
Turn-On Time	t _{on}		90	—	ns	
Delay Time	t _d	_	10	_	ns	$I_{C} = -1A, I_{B1} = -I_{B2} = 50mA;$
Rise Time	tr	_	80	_	ns	T _A = +25°C

Note: 11. Measured under pulsed conditions. Pulse width \leq 300 $\mu s.$ Duty cycle ${\leq}2\%.$

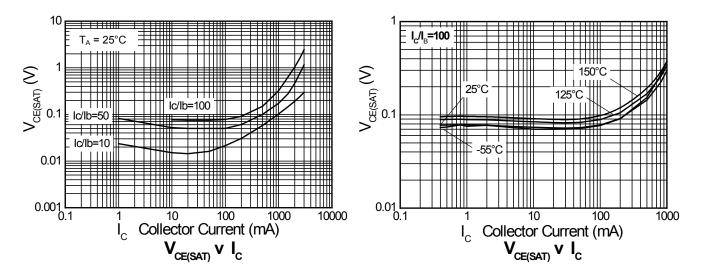


Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





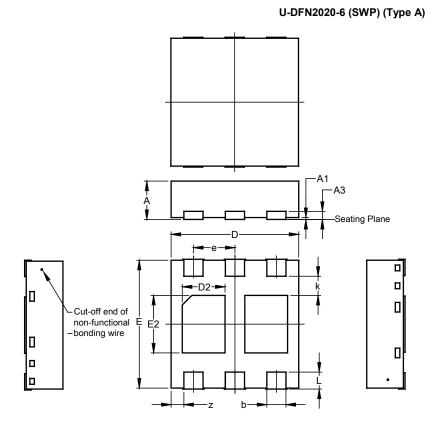
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)





Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

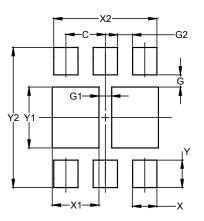


U-DFN2020-6 (SWP)						
	(Type A)					
Dim	Min	Max	Тур			
Α	0.55	0.65	0.60			
A1	0.00	0.05	0.03			
A3			0.127			
b	0.25	0.35	0.30			
D	1.95	2.05	2.00			
D2	0.57	0.77	0.67			
Е	1.95	2.05	2.00			
E2	0.80	1.00	0.90			
е	0.65BSC					
k	0.30BSC					
L	0.22	0.32	0.27			
z 0.20BSC						
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (SWP) (Type A)



Dimensions	Value
Dimensions	(in mm)
С	0.650
G	0.200
G1	0.210
G2	0.250
Х	0.400
X1	0.770
X2	1.700
Y	0.450
Y1	1.000
Y2	2.300



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